



Description

The FDD86113LZ uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

$V_{DS} = 100V$ $I_D = 20A$

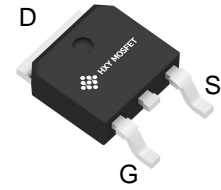
$R_{DS(ON)} < 87m\Omega$ @ $V_{GS}=10V$

Application

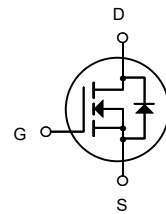
Battery protection

Load switch

Uninterruptible power supply



TO-252-2L



N-Channel MOSFET

Ordering Information

Product ID	Pack	Brand	Qty(PCS)
FDD86113LZ	TO-252-2L	HXY MOSFET	2500

Absolute Maximum Ratings $T_c=25^\circ C$ unless otherwise noted

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	100	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_c=25^\circ C$	Continuous Drain Current, V_{GS} @ 10V	20	A
$I_D@T_c=100^\circ C$	Continuous Drain Current, V_{GS} @ 10V	10	A
I_{DM}	Pulsed Drain Current	30	A
EAS	Single Pulse Avalanche Energy	6.1	mJ
I_{AS}	Avalanche Current	15	A
$P_D@T_c=25^\circ C$	Total Power Dissipation	34.7	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$
$R_{\theta JA}$	Thermal Resistance Junction-ambient	62	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case	3.6	$^\circ C/W$



Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	100	---	---	V
$\Delta BV_{DSS}/\Delta T$	BVDSS Temperature Coefficient	Reference to 25°C , $I_D=1mA$	---	0.098	---	$V/^\circ\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=10V, I_D=10A$	---	80	87	$m\Omega$
		$V_{GS}=4.5V, I_D=8A$	---	95	105	$m\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\mu A$	1.0	---	2.5	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-4.57	---	$mV/^\circ\text{C}$
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=80V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	1	μA
		$V_{DS}=80V, V_{GS}=0V, T_J=55^\circ\text{C}$	---	---	5	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=5V, I_D=10A$	---	13	---	S
R_g	Gate Resistance	$V_{DS}=0V, V_{GS}=0V, f=1MHz$	---	2	---	Ω
Q_g	Total Gate Charge (10V)	$V_{DS}=80V, V_{GS}=10V, I_D=10A$	---	26.2	---	nC
Q_{gs}	Gate-Source Charge		---	4.6	---	
Q_{gd}	Gate-Drain Charge		---	5.1	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=50V, V_{GS}=10V, R_G=3.3\Omega$ $I_D=10A$	---	4.2	---	ns
T_r	Rise Time		---	8.2	---	
$T_{d(off)}$	Turn-Off Delay Time		---	35.6	---	
T_f	Fall Time		---	9.6	---	
C_{iss}	Input Capacitance	$V_{DS}=15V, V_{GS}=0V, f=1MHz$	---	1535	---	pF
C_{oss}	Output Capacitance		---	60	---	
C_{rss}	Reverse Transfer Capacitance		---	37	---	
I_S	Continuous Source Current ^{1,5}	$V_G=V_D=0V$, Force Current	---	---	20	A
I_{SM}	Pulsed Source Current ^{2,5}		---	---	30	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V, I_S=1A, T_J=25^\circ\text{C}$	---	---	1.2	V
t_{rr}	Reverse Recovery Time	$I_F=10A, di/dt=100A/\mu s, T_J=25^\circ\text{C}$	---	37	---	nS
Q_{rr}	Reverse Recovery Charge		---	27.3	---	nC

Note :

- 1.The data tested by surface mounted on a 1 inch²FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is $V_{DD}=25V, V_{GS}=10V, L=0.1mH, I_{AS}=11A$
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.



Typical Characteristics

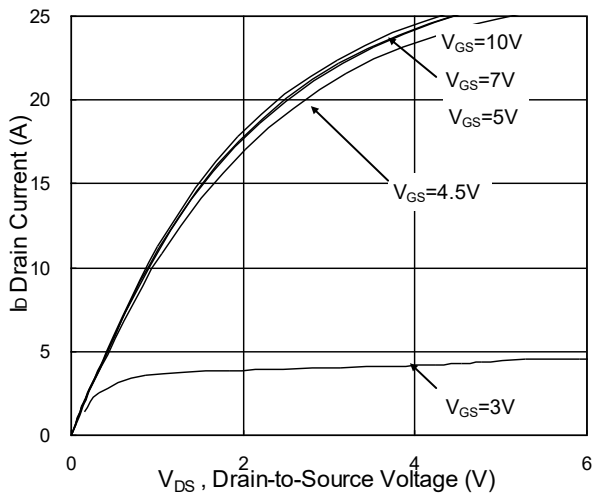


Fig.1 Typical Output Characteristics



Fig.2 On-Resistance vs. Gate-Source

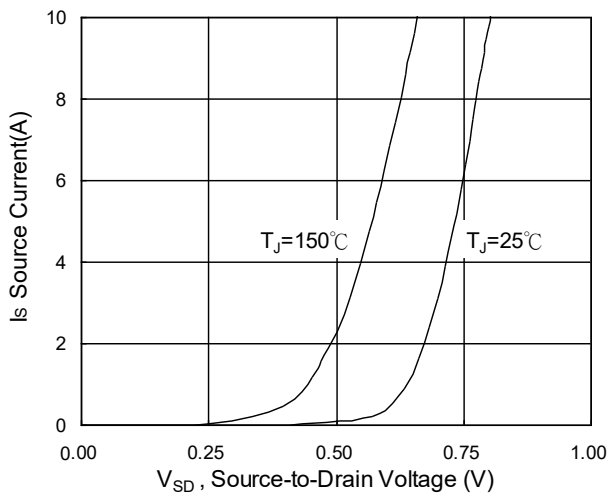


Fig.3 Forward Characteristics Of Reverse

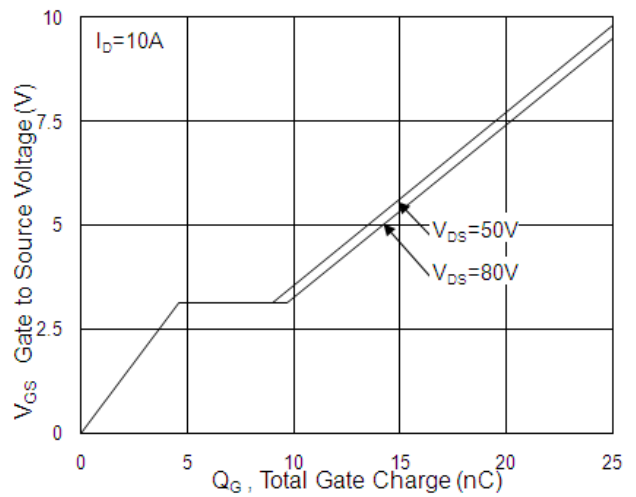


Fig.4 Gate-Charge Characteristics

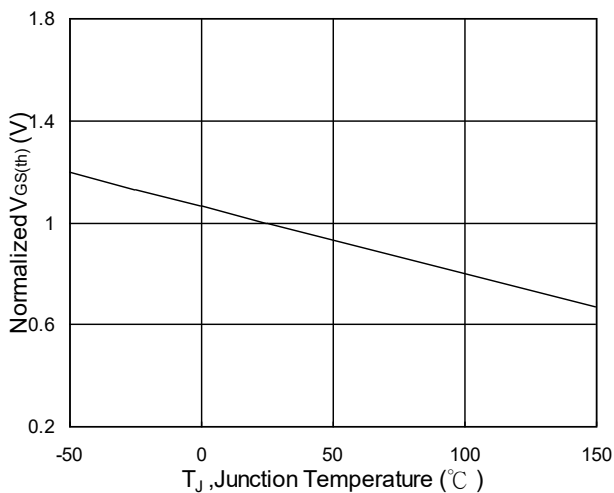


Fig.5 Normalized V_{GS(th)} vs. T_J

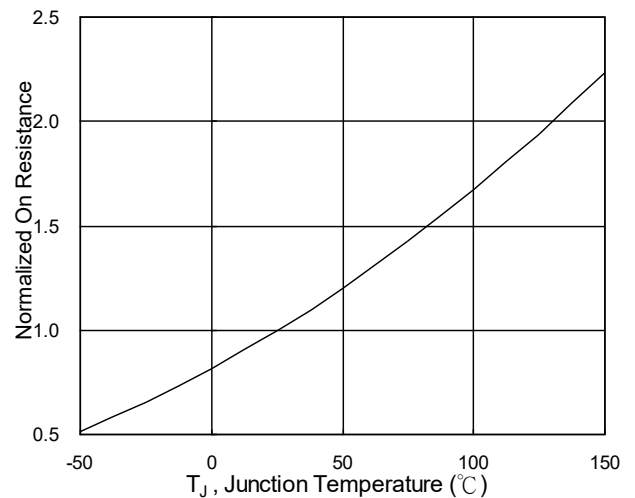


Fig.6 Normalized R_{DS(on)} vs. T_J

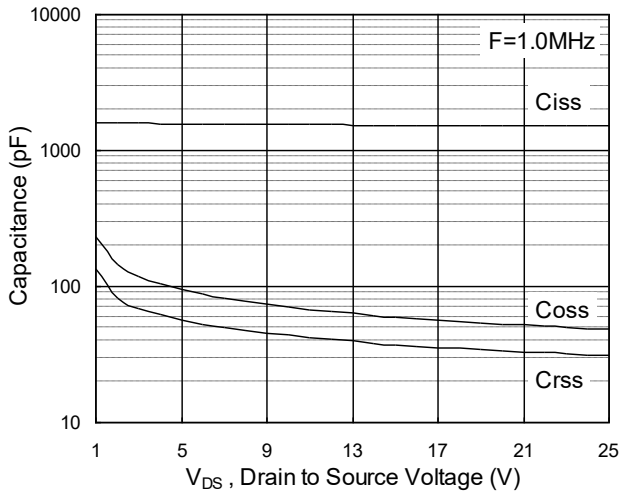


Fig.7 Capacitance

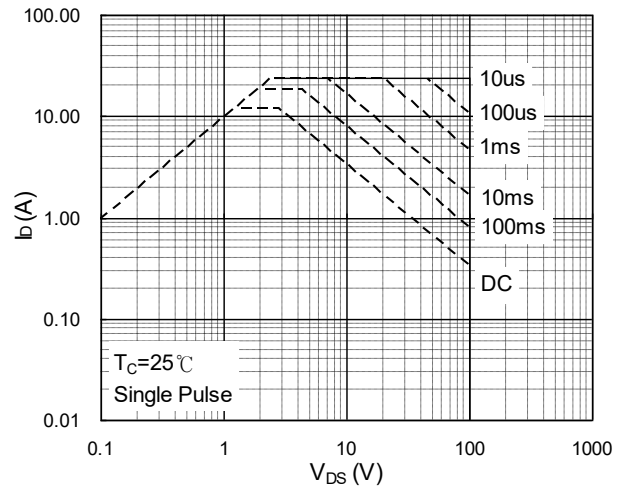


Fig.8 Safe Operating Area

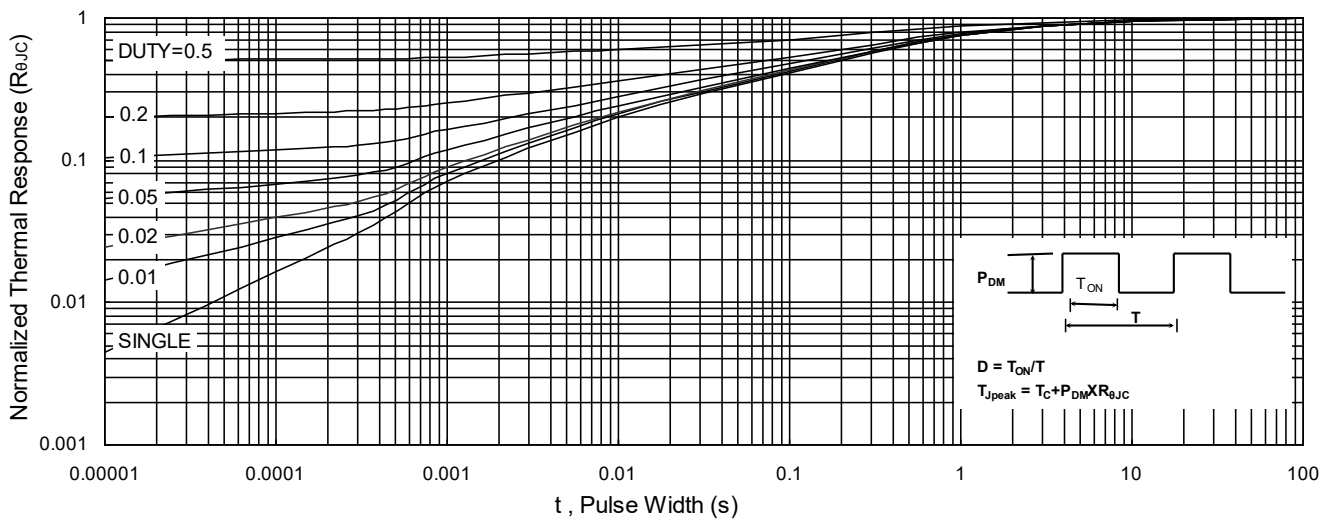


Fig.9 Normalized Maximum Transient Thermal Impedance



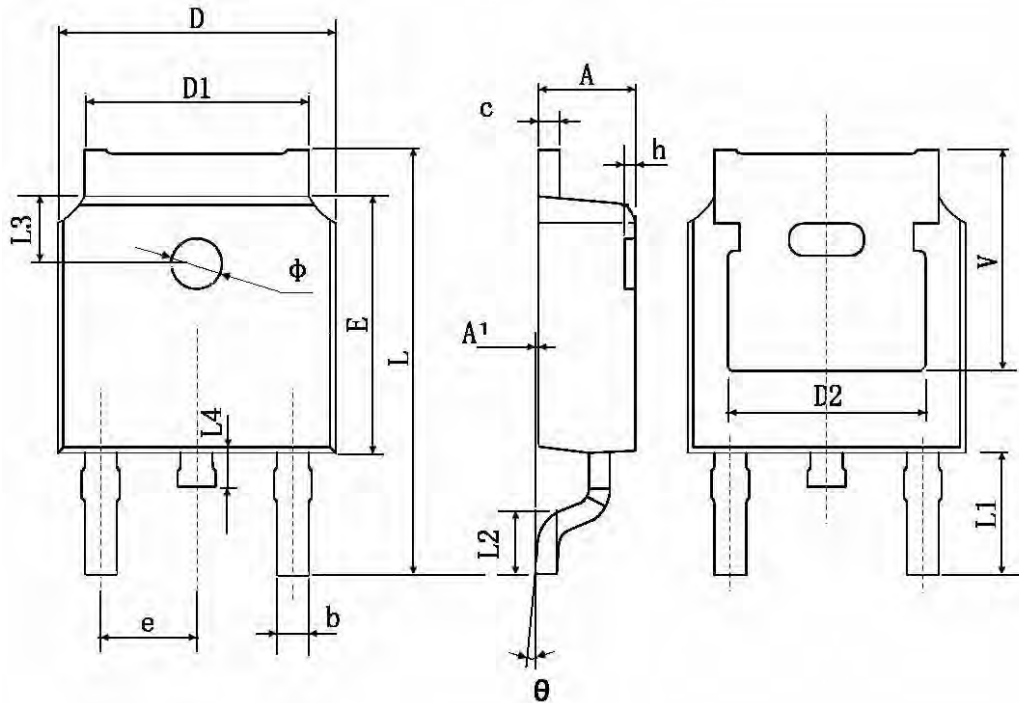
Fig.10 Switching Time Waveform



Fig.11 Unclamped Inductive Switching Waveform



TO-252-2L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	0.483 TYP.		0.190 TYP.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 TYP.		0.114 TYP.	
L2	1.400	1.700	0.055	0.067
L3	1.600 TYP.		0.063 TYP.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 TYP.		0.211 TYP.	



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